

# p-channel JFET designed for . . .



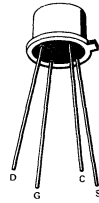
Performance Curves PC  
See Section 4

## ■ General Purpose Amplifiers

### \*ABSOLUTE MAXIMUM RATINGS (25°C)

- Gate-Drain or Gate-Source Voltage (Note 1) . . . . . 20 V
- Drain-Source Voltage . . . . . -20 V
- Gate Current . . . . . 10 mA
- Total Device Dissipation at (or below)  
25°C Free-Air Temperature (Note 2) . . . . . 300 mW
- Storage Temperature Range . . . . . -65 to +200°C
- Lead Temperature 1/16" From Case For 10 Sec . . . . 300°C

TO-72  
See Section 5



### \* ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic	2N3909		Unit	Test Conditions	
	Min	Max			
1   I <sub>GSS</sub>   Gate Reverse Current		10	nA	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0 T = 100°C	
2   S		1	μA		
3   B   BV <sub>GSS</sub>   Gate-Source Breakdown Voltage	20			I <sub>G</sub> = 10 μA, V <sub>DS</sub> = 0	
4   T   V <sub>GS(off)</sub>   Gate-Source Cutoff Voltage		8.0	v	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 μA	
5   C   V <sub>GS</sub>   Gate-Source Voltage	0.3	7.9		V <sub>DS</sub> = -10 V, I <sub>D</sub> = -30 μA	
6   I <sub>DSS</sub>   Saturation Drain Current	-0.3	-15	mA		
7   g <sub>fs</sub>   Common-Source Forward Transconductance	1,000	5,000		V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0	
8   g <sub>os</sub>   Common-Source Output Conductance		100	μmho		f = 1 kHz
9    y <sub>fs</sub>     Common-Source Forward Transadmittance	900				f = 10 MHz
10   C <sub>iss</sub>   Common-Source Input Capacitance		32			f = 1 MHz
11   C <sub>rss</sub>   Common-Source Reverse Transfer Capacitance		16	pF		

PC

\* JEDEC registered data

**Notes**

- 1 Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
- 2 Derate linearly to 175°C free-air temperature at rate of 2 mW/°C.